

AMENDMENTS TO THE CLAIMS

Claim 1 (Currently amended): A method of correcting a mask layout, the mask layout comprising a plurality 5 of line patterns, the method comprising:

providing line width deviation data of transferred line patterns, the line width deviation comprising a deviation of an after-etch-inspection critical dimension of the transferred line patterns onto a wafer;
10 executing an inspection program to classify the line patterns of the mask layout into at least a first-type line pattern and a second-type line pattern according to the line width deviation data of the transferred line patterns ~~a pattern density of the line patterns;~~
15 and

making a line width correction of a first constant value on the first-type line pattern and making a line width correction of a second constant value on the second-type line pattern;
20 ~~wherein the first constant value is determined by the line width deviation data of the first type line pattern, and the second constant value is determined by the line width deviation data of the second type line pattern.~~

25 Claim 2 (Original): The method of claim 1 wherein a pattern density of the first-type line pattern is different from a pattern density of the second-type line pattern.

30 Claim 3 (Original): The method of claim 2 wherein the pattern density is determined by a distance between

two adjacent line patterns.

Claim 4 (Original): The method of claim 1 wherein the line width deviation is a result of a systematic error.

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Claim 5 (Original): The method of claim 1 wherein the line width deviation is a result of a micro-loading effect.

10 Claim 6 (Cancelled)

Claim 7 (Original): The method of claim 1 wherein the first-type line pattern comprises dense patterns or semi-dense patterns, and the second-type line pattern 15 comprises isolated patterns.

Claim 8 (Original): The method of claim 1 wherein the first-type line pattern comprises isolated patterns or semi-isolated patterns, and the second-type line 20 pattern comprises dense patterns.

Claim 9 (Original): The method of claim 1 wherein the line width correction of the first constant value and the line width correction of the second constant value 25 comprise increasing line widths of the line patterns or decreasing the line widths of the line patterns.

Claim 10 (Original): The method of claim 1 wherein each of the line patterns is used for defining a conductive 30 area.

[[1.]] Claim 11 (Currently amended): A method of

correcting a mask layout, the mask layout comprising a plurality of element patterns, the method comprising: providing pattern deviation data of transferred element patterns, the pattern deviation comprising a 5 deviation of an after-etch-inspection critical dimension of the transferred element patterns onto a wafer;

executing an inspection program to classify the element patterns of the mask layout into at least a 10 first-type element pattern and a second-type element pattern according to the pattern deviation data—pattern density of the transferred element patterns; and

making a selective correction on the first-type 15 element pattern and the second-type element pattern, respectively;

~~—wherein the selective correction determines a correction value on the first-type element pattern and on the second-type element pattern according to the 20 pattern deviation data of the first-type element pattern and of the second-type element pattern, respectively.~~

1. Claim 12 (Currently amended): The method of claim 25 [[10]] 11 wherein the element patterns comprise line patterns.

1. Claim 13 (Canceled)

30 1. Claim 14 (Currently amended): The method of claim [[11]] 12 wherein the selective correction comprises increasing line widths of the line patterns or

decreasing the line widths of the line patterns.

1. Claim 15 (Currently amended): The method of claim
[[10]] 11 wherein the pattern deviation is a result
5 of a systematic error.

1. Claim 16 (Currently amended): The method of claim
[[10]] 11 wherein the pattern deviation is a result
of a micro-loading effect.

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4. Claim 17 (Canceled)

1. Claim 18 (Currently amended): The method of claim
[[10]] 11 wherein the first-type element pattern
15 comprises dense patterns or semi-dense patterns, and
the second-type element pattern comprises isolated
patterns.

20 1. Claim 19 (Currently amended): The method of claim
[[10]] 11 wherein the first-type element pattern
comprises isolated patterns or semi-isolated patterns,
and the second-type element pattern comprises dense
patterns.

25 1. Claim 20 (Currently amended): The method of claim
[[10]] 11 wherein each of the element patterns is used
to define a conductive area.

Claims 21-29 (Canceled)

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